Ordering number:676D

PNP/NPN Epitaxial Planar Silicon Transistors



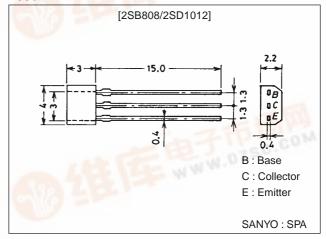
# 2SB808/2SD1012

# Low-Voltage Large-Current Amplifier Applications

## **Package Dimensions**

unit:mm

2033



():2SB808

# **Specifications**

## Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit	
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)20	V	
Collector-to-Emitter Voltage	V <sub>CEO</sub>		(-)15	V	
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)5	V	
Collector Current	I <sub>C</sub>	Total T	(-)0.7	Α	
Collector Current (Pulse)	ICP	- A.D. (1977)	(–)1.5	А	
Collector Dissipation	PC	-21 FF 1 -25	250	mW	
Junction Temperature	Tj		125	°C	
Storage Temperature	Tstg		-55 to +125	°C	

# Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Unit		
Falametel		Conditions		typ	max	Offic
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)15V, I <sub>E</sub> =0			(-)1.0	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(-)1.0	μΑ
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)50mA	160*		960*	77
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)500mA Pulse	80			.01
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA		250		MHz
Common Base Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz	AL W	(13)		pF
				8		pF

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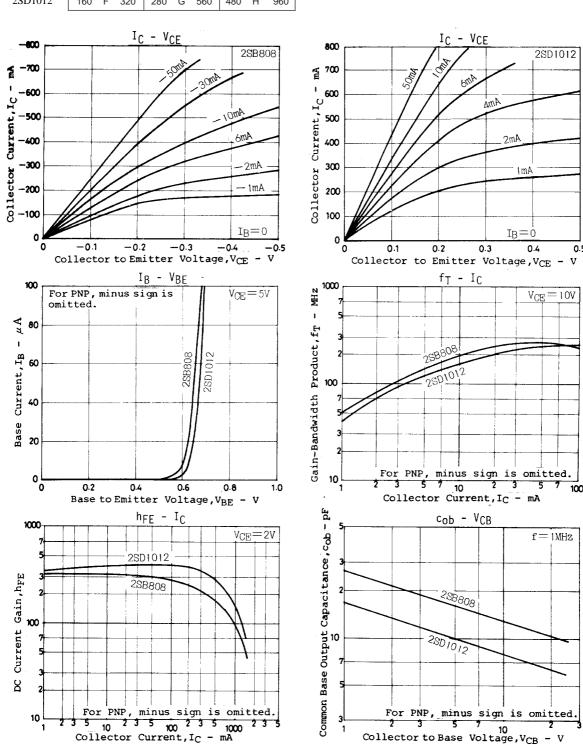
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

## 2SB808/2SD1012

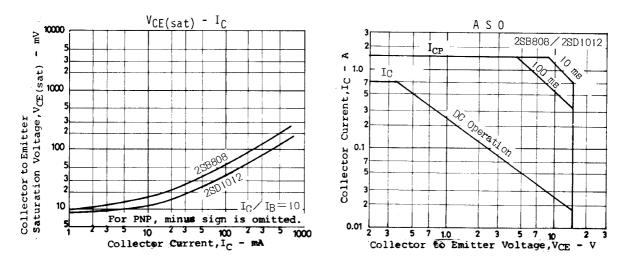
Parameter	Symbol	Conditions		Unit		
raiametei	Symbol	Conditions		typ	max	Offic
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub> 1	I <sub>C</sub> =(-)5mA, I <sub>B</sub> =(-)0.5mA		(-15)	(–35)	mV
				10	25	mV
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub> <sup>2</sup>	I <sub>C</sub> =(-)100mA, I <sub>B</sub> =(-)10mA		(-60)	(-120)	mV
				30	80	mV
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)100mA, I <sub>B</sub> =(-)10mA		(-)0.8	(-)1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)10μA, I <sub>E</sub> =0	(–)20			V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(–)15			V
Emitter-to-Base Breakdown Votage	V <sub>(BR)EBO</sub>	$I_E=(-)10\mu A, I_C=0$	(–)5			V

 $\mbox{\ensuremath{^{*}}}$  : The 2SB808/2SD1012 are classified by 50mA  $\mbox{\ensuremath{h_{FE}}}$  as follows :

2SB808	160	F	320	280	G	560			
2SD1012	160	F	320	280	G	560	480	Н	960



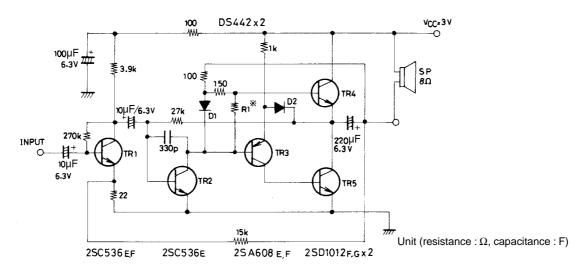
### 2SB808/2SD1012



Sample Application Circuit : Low-voltage 3V ( $P_O$  120mW) ITL-OTL power amplifier.

#### · Circuit configuration

For obtaining an output of more than 100mW, the middle-point voltage at the output stage and the collector voltage of the driver transistor must be  $V_{CC}/2$ . Therefore, the output stage is of quasi complementary configuration composed of npn/npn transistors. The phase is reversed by the 2SA608 and the middle-point voltage are the output stage and the collector voltage of the driver transistor are more to be  $V_{CC}/2$  so that the output can be maximized.



R<sub>1</sub>: Used control idle current

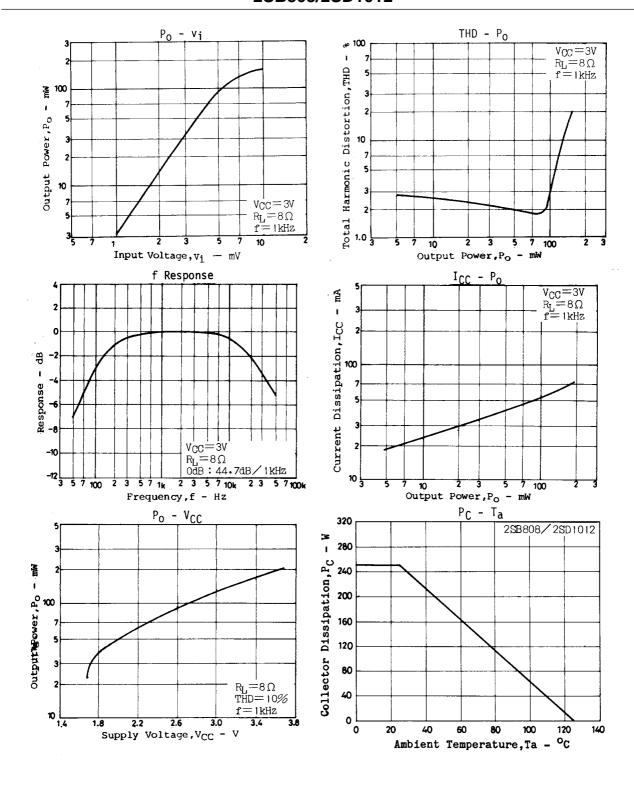
For  $R_1$ =820 $\Omega$ , use rank F for [TR4, 5 (2SD1012)].

For  $R_1$ =680 $\Omega$ , use rank G for [TR4, 5 (2SD1012)].

### **Main Specifications**

Characteristic	Conditions	f=400Hz	f=1kHz	Unit
Current dissipation	Quiescent, total current dissipation	11.0 to 15.5	11.0 to 15.5	mA
Output power	THD=10%	120 to 125	127 to 130	mW
Votlage gain	P <sub>O</sub> =10mW	43.3 to 45.5	43.5 to 45.7	dB
Total harmonic distortion	P <sub>O</sub> =50mW	1.4 to 2.6	1.3 to 2.5	%
Input resistance	P <sub>O</sub> =10mW	10.4 to 20.5	11.0 to 21.0	kΩ

Note : for above-mentioned  $h_{\mbox{\scriptsize FE}}$  rank.



#### 2SB808/2SD1012

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